

L Number	Hits	Search Text	DB	Time stamp
1	12855	(dielectric or insulative or insulating or insulator) same metal same polysilicon	USPAT; US-PGPUB	2004/06/24 16:06
2	325	((dielectric or insulative or insulating or insulator) same metal same polysilicon) same (prevent or preventing) same (diffusion or reaction or interface or interfacial)	USPAT; US-PGPUB	2004/06/24 16:07
3	311	((((dielectric or insulative or insulating or insulator) same metal same polysilicon) same (prevent or preventing) same (diffusion or reaction or interface or interfacial)) and (gate or electrode)	USPAT; US-PGPUB	2004/06/24 16:07
4	165	(((((dielectric or insulative or insulating or insulator) same metal same polysilicon) same (prevent or preventing) same (diffusion or reaction or interface or interfacial)) and (gate or electrode)) and capacitor	USPAT; US-PGPUB	2004/06/24 16:08
5	159	(((((dielectric or insulative or insulating or insulator) same metal same polysilicon) same (prevent or preventing) same (diffusion or reaction or interface or interfacial)) and (gate or electrode)) and capacitor) and @ad<20030312	USPAT; US-PGPUB	2004/06/24 18:00
6	159	(((((dielectric or insulative or insulating or insulator) same metal same polysilicon) same (prevent or preventing) same (diffusion or reaction or interface or interfacial)) and (gate or electrode)) and capacitor) and @ad<20030312	USPAT; US-PGPUB	2004/06/24 17:54

	U	1 [1 j]	Docum nt ID	Issue Dat	Pag s	Titl	Current OR	Current XR f	Retrieval Classif
1	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040043578 A1	20040304	17	Platinum stuffed with silicon oxide as a diffusion oxygen barrier for semiconductor devices	438/396		
2	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20030094646 A1	20030522	6	Semiconductor device and method for manufacturing semiconductor device	257/306	257/296; 257/751; 257/E21.02 1; 438/244; 438/253; 438/387; 438/627	
3	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20030003641 A1	20030102	10	Method of forming memory device	438/200	257/E21.02 1	
4	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20020177268 A1	20021128	9	Novel high-K dielectric materials and processes for manufacturing them	438/200		
5	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20020025626 A1	20020228	8	Integrated dielectric and method	438/240	257/E21.00 9; 257/E21.19 3; 257/E29.16 5	
6	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6656839 B2	20031202	8	Solutions of metal-comprising materials, and methods of making solutions of metal-comprising materials	438/681	118/715; 257/E21.00 9; 257/E21.17 ; 427/255.11 ; 438/393; 438/396	

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7	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6639288 B1	20031028	50	Semiconductor device with a particular conductor arrangement	257/412	257/386; 257/E21.196; 257/E21.434; 257/E21.583; 257/E21.584; 257/E21.633; 257/E21.634; 257/E21.635; 257/E21.657; 257/E29.152	
8	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6586161 B2	20030701	39	Mass production method of semiconductor integrated circuit device and manufacturing method of electronic device	430/311	216/83; 257/E21.309; 427/250; 427/252; 427/253; 427/576; 430/330; 438/405; 438/459	
9	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6555863 B1	20030429	11	Semiconductor circuit constructions, capacitor constructions, and methods of forming semiconductor circuit constructions and capacitor constructions	257/304	257/311; 257/E21.01; 257/E21.021	

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10	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6514826 B1	20030204	4	Method of forming a gate electrode in a semiconductor device	438/287	257/E21.19 3; 257/E21.27 4; 257/E29.16 2; 438/197; 438/240; 438/585	
11	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6465319 B1	20021015	15	Aluminum-filled self-aligned trench for stacked capacitor structure and methods	438/387	257/751; 257/754; 257/E21.01 9; 257/E21.65 8; 438/253; 438/396; 438/627	
12	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6387748 B1	20020514	11	Semiconductor circuit constructions, capacitor constructions, and methods of forming semiconductor circuit constructions and capacitor constructions	438/239	257/E21.01 ; 257/E21.02 1; 438/240; 438/253; 438/261	
13	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6365517 B1	20020402	5	Process for depositing thin films containing titanium and nitrogen	438/683	257/E21.02 1; 257/E21.17 ; 257/E21.58 4; 438/680; 438/685	

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14	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6319832 B1	20011120	9	Methods of making semiconductor devices	438/681	257/E21.00 9; 257/E21.17 ; 427/255.11 ; 427/255.12 ; 438/393; 438/396	
15	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6165863 A	20001226	14	Aluminum-filled self-aligned trench for stacked capacitor structure and methods	438/387	257/E21.01 9; 257/E21.65 8; 438/244; 438/655	